using the resist pattern as a mask; removing the resist pattern; removing a surface layer of the wiring to a depth of at least 5 nm to thin the wiring; and forming a metal silicide film on a surface of the wiring by causing reaction between a surface layer of the thinned wiring and a refractory metal which reacts with silicon to form silicide.

A2

Please replace the paragraph from page 2, line 24 to page 3, line 9 with the following rewritten paragraph:

A3

According to another aspect of the present invention, there is provided a method for manufacturing a semiconductor device, comprising the steps of: forming wiring comprising silicon on a surface of a semiconductor substrate; covering part of the wiring with a resist pattern; implanting ions into the wiring using the resist pattern as a mask; removing the resist pattern; oxidizing the wiring beginning on an upper surface thereof down to a predetermined depth; removing an oxidized section of the wiring oxidized in the oxidizing step and thereby thinning the wiring; and forming a metal silicide film on a surface of the wiring by causing reaction between a surface section of the thinned wiring and a refractory metal which reacts with silicon to form silicide.

Please replace the paragraph at page 8, lines 11-21 with the following rewritten paragraph:

A4

As shown in Fig. 2E, a cobalt silicide film 25 is formed on an upper surface of the wiring 3. Description will now be given of a method of forming the cobalt silicide film 25. A 10 nm thick cobalt (Co) film and a 30 nm thick titanium nitride (TiN) film are deposited on the overall surface of the silicon substrate